

BCY78, VII, VIII, IX, X
BCY79, VII, VIII, IX, X

**SILICON
PNP TRANSISTORS**



TO-18 CASE



www.centra-semi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR BCY78 and BCY79 series types are silicon PNP epitaxial planar transistors, mounted in a hermetically sealed metal case, designed for low noise amplifier and switching applications.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$ unless otherwise noted)		SYMBOL	BCY78	BCY79	UNITS
Collector-Base Voltage		V_{CB0}	32	45	V
Collector-Emitter Voltage		V_{CEO}	32	45	V
Emitter-Base Voltage		V_{EBO}	5.0		V
Continuous Collector Current		I_C	100		mA
Peak Collector Current		I_{CM}	200		mA
Peak Base Current		I_{BM}	200		mA
Power Dissipation		P_D	340		mW
Power Dissipation ($T_C=25^\circ\text{C}$)		P_D	1.0		W
Operating and Storage Junction Temperature		T_J, T_{stg}	-65 to +200		$^\circ\text{C}$
Thermal Resistance		θ_{JA}	450		$^\circ\text{C/W}$
Thermal Resistance		θ_{JC}	150		$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CBO}	$V_{CB}=\text{Rated } V_{CB0}$		15	nA
I_{CBO}	$V_{CB}=\text{Rated } V_{CB0}, T_A=150^\circ\text{C}$		10	μA
I_{EBO}	$V_{EB}=5.0\text{V}$		20	nA
BV_{CBO}	$I_C=10\mu\text{A}$ (BCY78)	32		V
BV_{CBO}	$I_C=10\mu\text{A}$ (BCY79)	45		V
BV_{CEO}	$I_C=2.0\text{mA}$ (BCY78)	32		V
BV_{CEO}	$I_C=2.0\text{mA}$ (BCY79)	45		V
BV_{EBO}	$I_E=1.0\mu\text{A}$	5.0		V
$V_{CE(\text{SAT})}$	$I_C=10\text{mA}, I_B=250\mu\text{A}$		0.25	V
$V_{CE(\text{SAT})}$	$I_C=100\text{mA}, I_B=2.5\text{mA}$		0.80	V
$V_{BE(\text{SAT})}$	$I_C=10\text{mA}, I_B=250\mu\text{A}$	0.60	0.85	V
$V_{BE(\text{SAT})}$	$I_C=100\text{mA}, I_B=2.5\text{mA}$	0.70	1.20	V
$V_{BE(\text{ON})}$	$V_{CE}=5.0\text{V}, I_C=2.0\text{mA}$	0.60	0.75	V

		BCY78-VII BCY79-VII			BCY78-VIII BCY79-VIII		BCY78-IX BCY79-IX		BCY78-X BCY79-X	
		MIN	TYP	MAX	MIN	MAX	MIN	MAX	MIN	MAX
h_{FE}	$V_{CE}=5.0\text{V}, I_C=10\mu\text{A}$	-	140	-	30	-	40	-	100	-
h_{FE}	$V_{CE}=5.0\text{V}, I_C=2.0\text{mA}$	120	-	220	180	310	250	460	380	630
h_{FE}	$V_{CE}=1.0\text{V}, I_C=10\text{mA}$	80	-	-	120	400	160	630	240	1000
h_{FE}	$V_{CE}=1.0\text{V}, I_C=100\text{mA}$	40	-	-	45	-	60	-	60	-

R4 (4-June 2013)

BCY78, VII, VIII, IX, X
BCY79, VII, VIII, IX, X

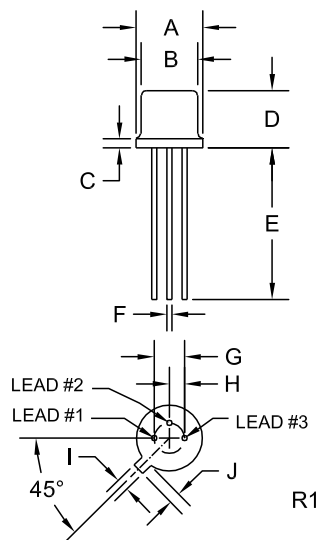
**SILICON
PNP TRANSISTORS**



ELECTRICAL CHARACTERISTICS - Continued: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
f_T	$V_{CE}=5.0\text{V}$, $I_C=10\text{mA}$, $f=100\text{MHz}$	100		MHz
C_{ob}	$V_{CB}=10\text{V}$, $I_E=0$, $f=1.0\text{MHz}$		7.0	pF
C_{ib}	$V_{EB}=0.5\text{V}$, $I_C=0$, $f=1.0\text{MHz}$		15	pF
NF	$V_{CE}=5.0\text{V}$, $I_C=0.2\text{mA}$, $R_S=2.0\text{k}\Omega$, $f=1.0\text{kHz}$, $B=200\text{Hz}$		10	dB
t_{on}	$V_{CC}=3.0\text{V}$, $I_C=10\text{mA}$, $I_{B1}=I_{B2}=1.0\text{mA}$		100	ns
t_d	$V_{CC}=3.0\text{V}$, $I_C=10\text{mA}$, $I_{B1}=I_{B2}=1.0\text{mA}$		50	ns
t_r	$V_{CC}=3.0\text{V}$, $I_C=10\text{mA}$, $I_{B1}=I_{B2}=1.0\text{mA}$		50	ns
t_{off}	$V_{CC}=3.0\text{V}$, $I_C=10\text{mA}$, $I_{B1}=I_{B2}=1.0\text{mA}$		700	ns
t_s	$V_{CC}=3.0\text{V}$, $I_C=10\text{mA}$, $I_{B1}=I_{B2}=1.0\text{mA}$		600	ns
t_f	$V_{CC}=3.0\text{V}$, $I_C=10\text{mA}$, $I_{B1}=I_{B2}=1.0\text{mA}$		100	ns
t_{on}	$V_{CC}=10\text{V}$, $I_C=100\text{mA}$, $I_{B1}=I_{B2}=10\text{mA}$		100	ns
t_d	$V_{CC}=10\text{V}$, $I_C=100\text{mA}$, $I_{B1}=I_{B2}=10\text{mA}$		35	ns
t_r	$V_{CC}=10\text{V}$, $I_C=100\text{mA}$, $I_{B1}=I_{B2}=10\text{mA}$		65	ns
t_{off}	$V_{CC}=10\text{V}$, $I_C=100\text{mA}$, $I_{B1}=I_{B2}=10\text{mA}$		400	ns
t_s	$V_{CC}=10\text{V}$, $I_C=100\text{mA}$, $I_{B1}=I_{B2}=10\text{mA}$		300	ns
t_f	$V_{CC}=10\text{V}$, $I_C=100\text{mA}$, $I_{B1}=I_{B2}=10\text{mA}$		100	ns

TO-18 CASE - MECHANICAL OUTLINE



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A (DIA)	0.209	0.230	5.31	5.84
B (DIA)	0.178	0.195	4.52	4.95
C	-	0.030	-	0.76
D	0.170	0.210	4.32	5.33
E	0.500	-	12.70	-
F (DIA)	0.016	0.019	0.41	0.48
G (DIA)	0.100		2.54	
H	0.050		1.27	
I	0.036	0.046	0.91	1.17
J	0.028	0.048	0.71	1.22

TO-18 (REV: R1)

LEAD CODE:

- 1) Emitter
- 2) Base
- 3) Collector

MARKING:
FULL PART NUMBER

R4 (4-June 2013)

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix " TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix " PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

Corporate Headquarters & Customer Support Team

Central Semiconductor Corp.
145 Adams Avenue
Hauppauge, NY 11788 USA
Main Tel: (631) 435-1110
Main Fax: (631) 435-1824
Support Team Fax: (631) 435-3388
www.centrasemi.com

Worldwide Field Representatives:
www.centrasemi.com/wwreps

Worldwide Distributors:
www.centrasemi.com/wwdistributors

For the latest version of Central Semiconductor's **LIMITATIONS AND DAMAGES DISCLAIMER**, which is part of Central's Standard Terms and Conditions of sale, visit: www.centrasemi.com/terms